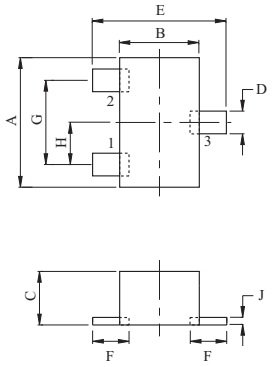
SWITCHING APPLICATION.



DIM	MILLIMETERS
A	1.60±0.20
B	0.85±0.10
C	0.70±0.10
D	0.27±0.10
E	1.60±0.10
F	0.39±0.10
G	1.00±0.10
H	0.50
J	0.13±0.05

1. EMITTER
2. BASE
3. COLLECTOR

ESM

FEATURES

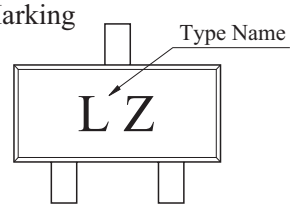
- High Current.
- Low $V_{CE(sat)}$.
  : $V_{CE(sat)} \leq 250mV$ at $I_C=200mA/I_B=10mA$.
- Complementary to KTA2012E.
- Suffix U : Qualified to AEC-Q101
  ex) KTC4072E-RTK/HU

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	15	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	500	mA
	I_{CP} *	1	A
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

* Single pulse Pw=1mS.

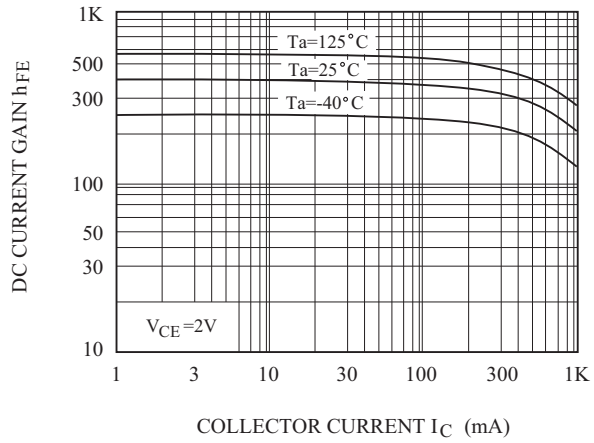
Marking



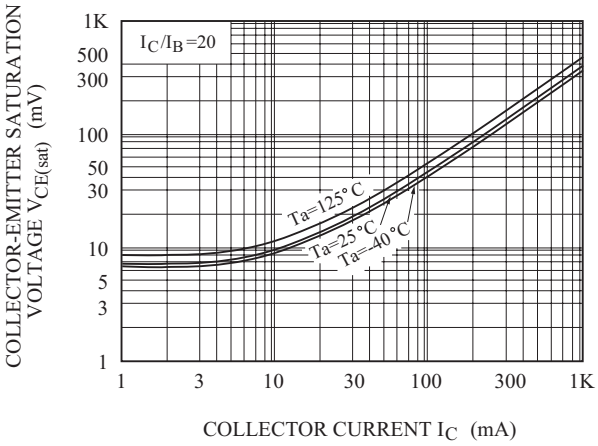
ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=15V$, $I_E=0$	-	-	100	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A$	15	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1mA$	12	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A$	6	-	-	V
DC Current Gain	h_{FE}	$V_{CE}=2V$, $I_C=10mA$	270	-	680	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=200mA$, $I_B=10mA$	-	90	250	mV
Transition Frequency	f_T	$V_{CE}=2V$, $I_C=10mA$, $f_T=100MHz$	-	320	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$, $I_E=0$, f=1MHz	-	7.5	-	pF

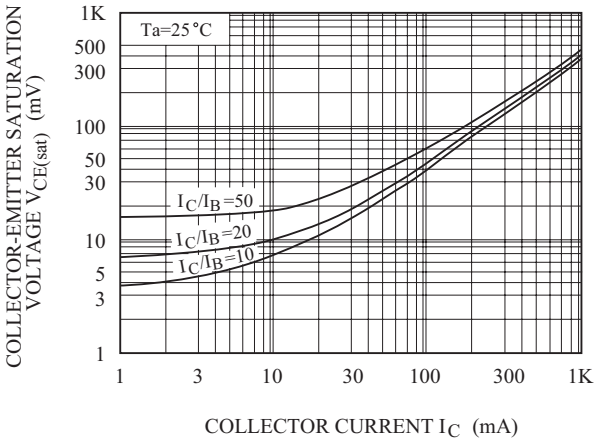
h_{FE} - I_C



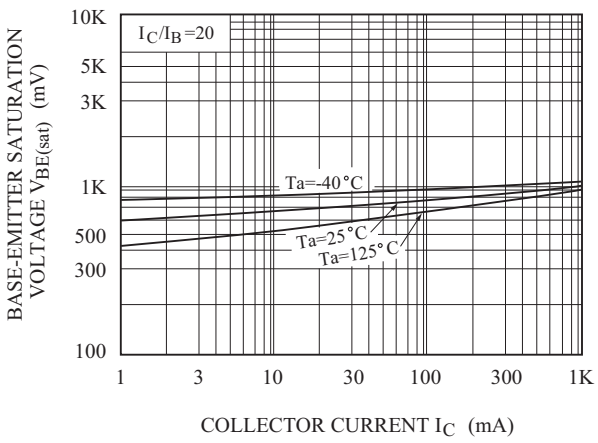
$V_{CE(sat)}$ - I_C



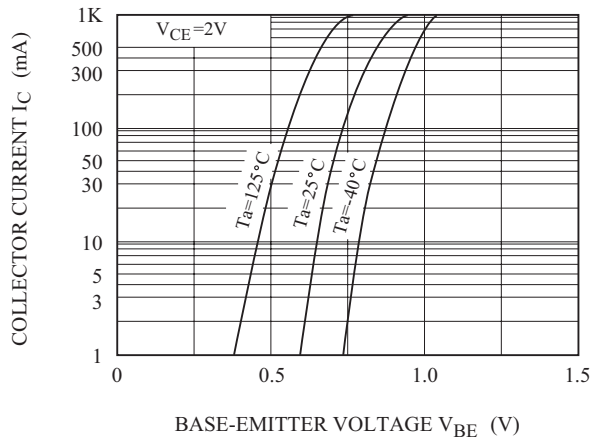
$V_{CE(sat)}$ - I_C



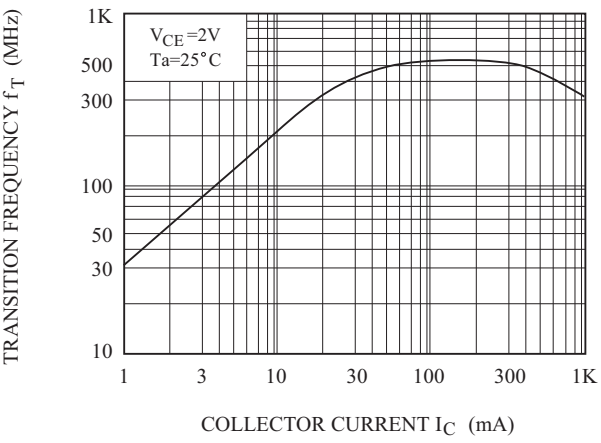
$V_{BE(sat)}$ - I_C



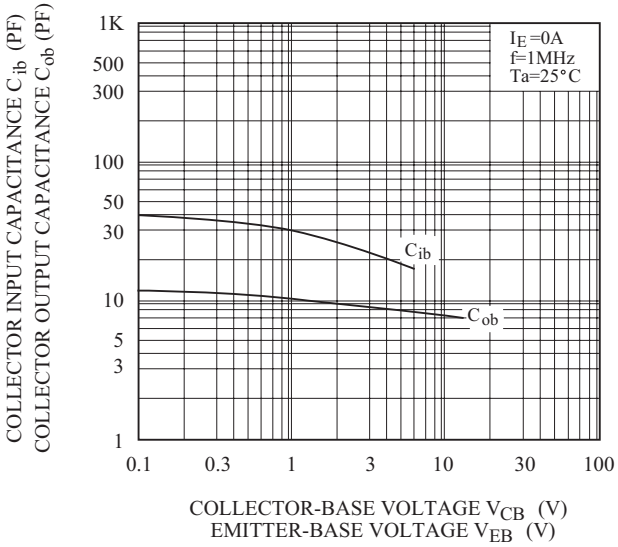
I_C - V_{BE}



f_T - I_C



C_{ob} - V_{CB} , C_{ib} - V_{EB}



Pc - Ta